

### General Description

The WSK250N03 is the highest performance trench N-ch MOSFET with extreme high cell density, which provide excellent RDSON and gate charge for most of the synchronous buck converter applications.

The WSK250N03 meet the RoHS and Green Product requirement, 100% EAS guaranteed with full function reliability approved.

### Features

- Advanced high cell density Trench technology
- Super Low Gate Charge
- Excellent CdV/dt effect decline
- 100% EAS Guaranteed
- Green Device Available

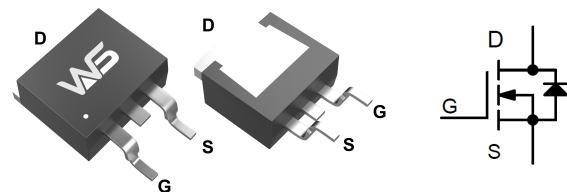
### Product Summary

BVDSS	RDSON	ID
30V	1.8mΩ	250A

### Applications

- High Frequency Point-of-Load Synchronous Buck Converter
- Networking DC-DC Power System

### TO-263-2L Pin Configuration



### Absolute Maximum Ratings

Symbol	Parameter	Rating	Units
$V_{DS}$	Drain-Source Voltage	30	V
$V_{GS}$	Gate-Source Voltage	$\pm 20$	V
$I_D@T_C=25^\circ C$	Continuous Drain Current, $V_{GS} @ 10V^1$	250	A
$I_D@T_C=100^\circ C$	Continuous Drain Current, $V_{GS} @ 10V^1$	180	A
$I_{DM}$	Pulsed Drain Current <sup>2</sup>	1000	A
EAS	Single Pulse Avalanche Energy <sup>3</sup>	600	mJ
$I_{AS}$	Avalanche Current	200	A
$P_D@T_C=25^\circ C$	Total Power Dissipation <sup>3</sup>	200	W
$P_D@T_C=100^\circ C$	Total Power Dissipation <sup>3</sup>	120	W
$T_{STG}$	Storage Temperature Range	-55 to 170	$^\circ C$
$T_J$	Operating Junction Temperature Range	-55 to 175	$^\circ C$

**Electrical Characteristics (T<sub>J</sub>=25 °C, unless otherwise noted)**

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
BV <sub>DSS</sub>	Drain-Source Breakdown Voltage	V <sub>GS</sub> =0V, I <sub>D</sub> =250uA	30	---	---	V
ΔBV <sub>DSS</sub> /ΔT <sub>J</sub>	BVDSS Temperature Coefficient	Reference to 25°C, I <sub>D</sub> =1mA	---	0.098	---	V/°C
R <sub>DS(ON)</sub>	Static Drain-Source On-Resistance <sup>2</sup>	V <sub>GS</sub> =10V, I <sub>D</sub> =145A	---	1.8	2.5	mΩ
		V <sub>GS</sub> =4.5V, I <sub>D</sub> =145A	---	2.5	3.5	mΩ
V <sub>GS(th)</sub>	Gate Threshold Voltage	V <sub>GS</sub> =V <sub>DS</sub> , I <sub>D</sub> =250uA	1	1.8	3	V
ΔV <sub>GS(th)</sub>	V <sub>GS(th)</sub> Temperature Coefficient		---	-6.57	---	mV/°C
I <sub>DSS</sub>	Drain-Source Leakage Current	V <sub>DS</sub> =24V, V <sub>GS</sub> =0V, T <sub>J</sub> =25°C	---	---	1	uA
		V <sub>DS</sub> =24V, V <sub>GS</sub> =0V, T <sub>J</sub> =55°C	---	---	2	
I <sub>GSS</sub>	Gate-Source Leakage Current	V <sub>GS</sub> =±20V, V <sub>DS</sub> =0V	---	---	±100	nA
g <sub>fs</sub>	Forward Transconductance	V <sub>DS</sub> =5V, I <sub>D</sub> =20A	28	---	---	S
Q <sub>g</sub>	Total Gate Charge (10V)	V <sub>DS</sub> =20V, V <sub>GS</sub> =10V, I <sub>D</sub> =120A	---	232	---	nC
Q <sub>gs</sub>	Gate-Source Charge		---	26	---	
Q <sub>gd</sub>	Gate-Drain Charge		---	59	---	
T <sub>d(on)</sub>	Turn-On Delay Time	V <sub>DD</sub> =15V, V <sub>GS</sub> =10V, R <sub>G</sub> =6Ω I <sub>D</sub> =145A, R <sub>L</sub> =30Ω	---	50	---	ns
T <sub>r</sub>	Rise Time		---	111	---	
T <sub>d(off)</sub>	Turn-Off Delay Time		---	88	---	
T <sub>f</sub>	Fall Time		---	74	---	
C <sub>iss</sub>	Input Capacitance	V <sub>DS</sub> =30V, V <sub>GS</sub> =0V, f=1MHz	---	10600	---	pF
C <sub>oss</sub>	Output Capacitance		---	1156	---	
C <sub>rss</sub>	Reverse Transfer Capacitance		---	732	---	

**Diode Characteristics**

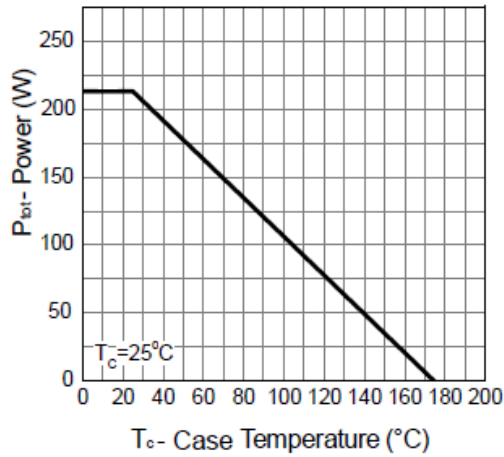
Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
I <sub>S</sub>	Continuous Source Current <sup>1,6</sup>	V <sub>G</sub> =V <sub>D</sub> =0V, Force Current	---	---	250	A
I <sub>SM</sub>	Pulsed Source Current <sup>2,6</sup>		---	---	300	A
V <sub>SD</sub>	Diode Forward Voltage <sup>2</sup>	V <sub>GS</sub> =0V, I <sub>S</sub> =1A, T <sub>J</sub> =25°C	---	---	1.2	V

Note :

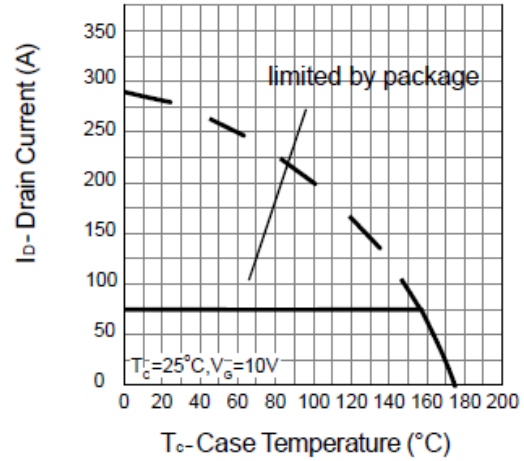
- The data tested by surface mounted on a 1 inch<sup>2</sup> FR-4 board with 2OZ copper, t<sub>≤</sub>10sec.
- The data tested by pulsed, pulse width ≤ 300us, duty cycle ≤ 2%
- The EAS data shows Max. rating. The test condition is V<sub>DD</sub>=25V, V<sub>GS</sub>=10V, L=0.5mH, I<sub>AS</sub>=20A
- The power dissipation is limited by 150°C junction temperature
- The Min. value is 100% EAS tested guarantee.
- The data is theoretically the same as I<sub>D</sub> and I<sub>DM</sub>, in real applications, should be limited by total power dissipation.

Typical Characteristics

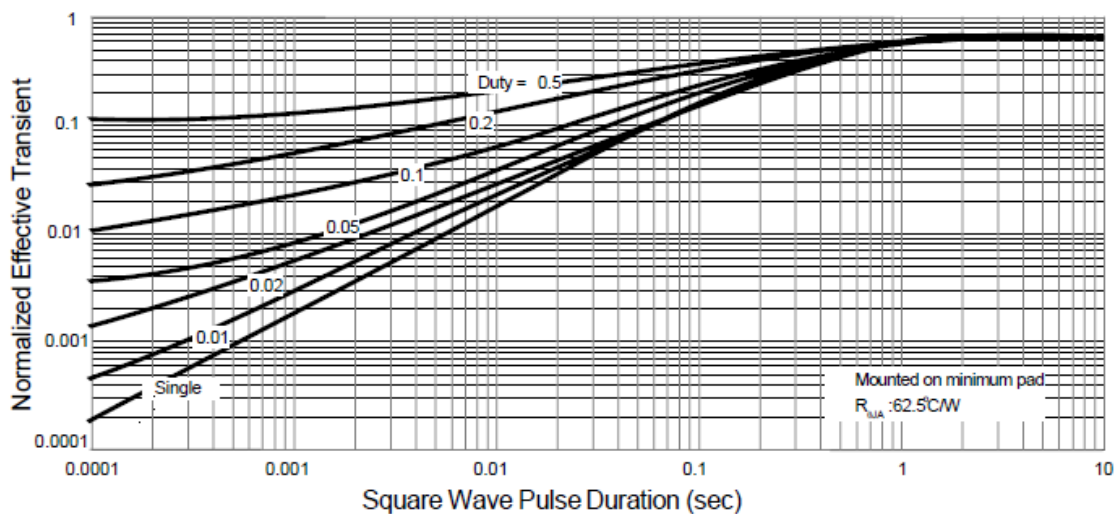
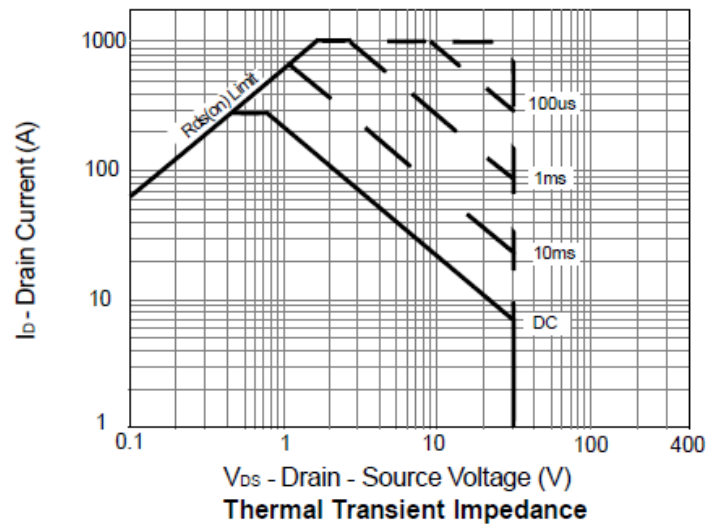
Power Dissipation



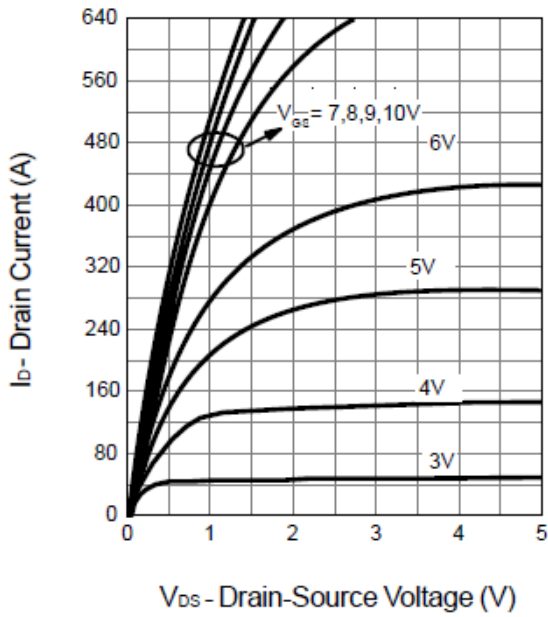
Drain Current



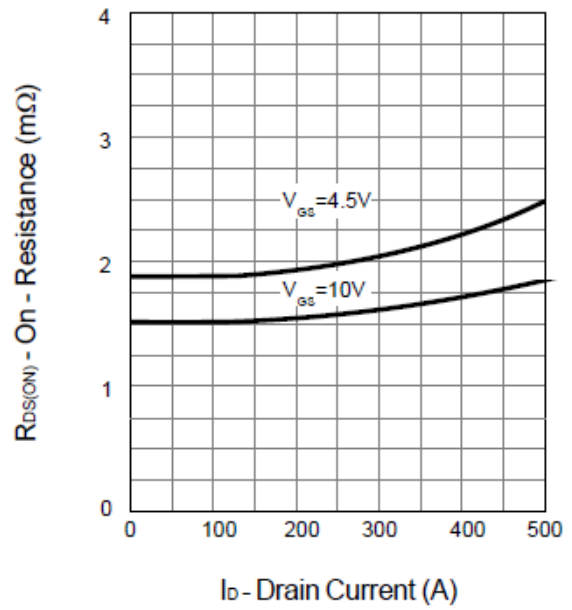
Safe Operation Area



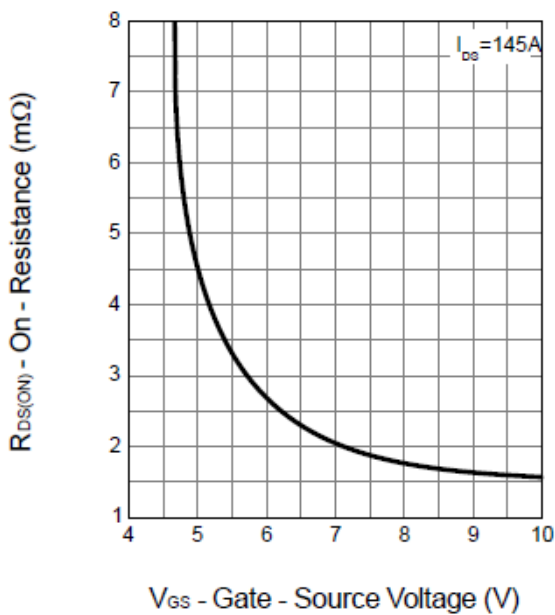
**Output Characteristics**



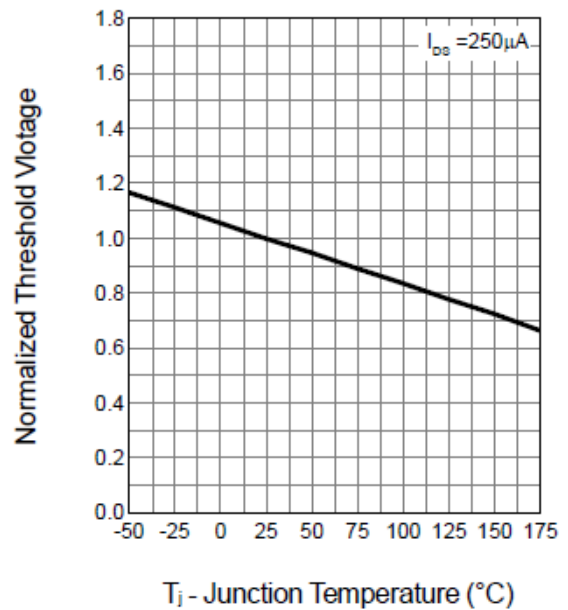
**Drain-Source On Resistance**



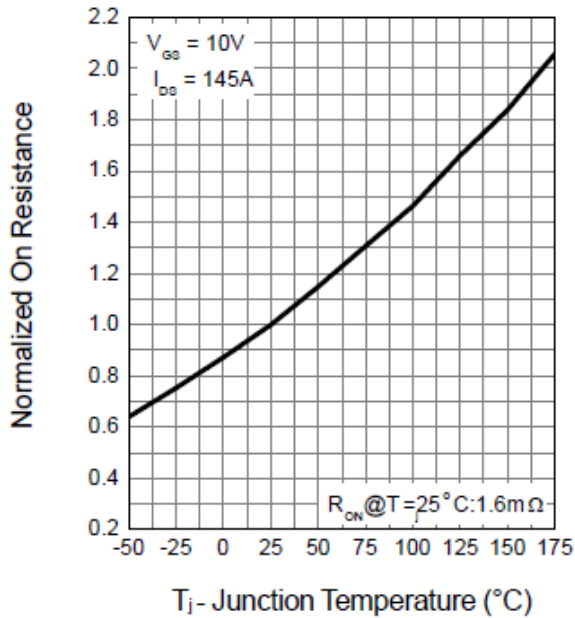
**Drain-Source On Resistance**



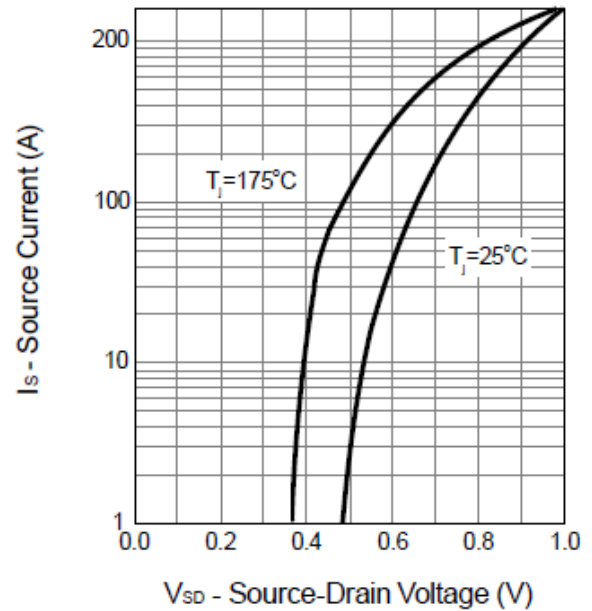
**Gate Threshold Voltage**



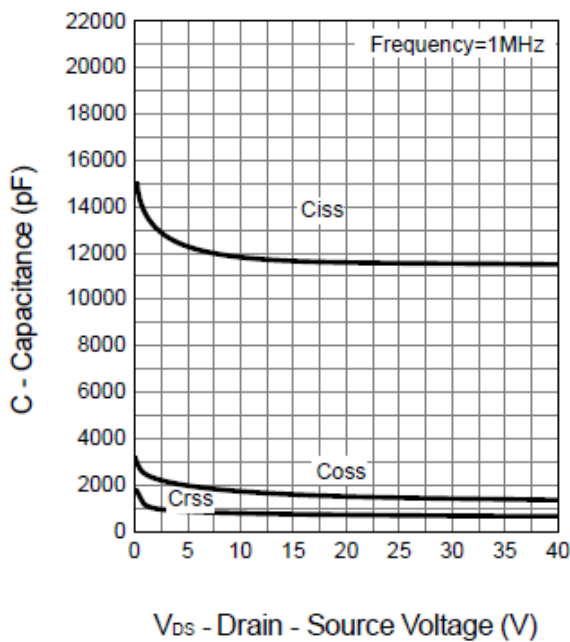
**Drain-Source On Resistance**



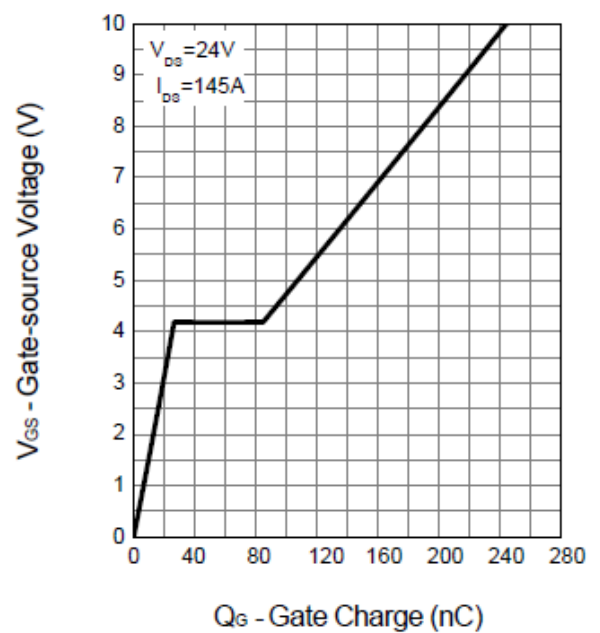
**Source-Drain Diode Forward**



**Capacitance**



**Gate Charge**





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